

Abstract

Method for double side polishing of at least one wafer of semiconductor material, comprising the following steps: placing the at least one wafer of semiconductor material in at least one carrier plate between an upper and a lower polishing platen of a double side polishing machine, the lower side of the upper polishing platen and the upper side of the lower polishing platen each being covered with a polishing pad; setting the at least one carrier plate, the upper polishing platen and the lower polishing platen in rotation; circulating a polish between a collecting vessel and the at least one wafer of semiconductor material disposed between the upper and lower polishing platens of the double side polishing machine; measuring the pH of the polish; and regulating the pH of the polish; characterized in that a target for the pH is not less than 11.4 and not more than 12.4 and the pH is regulated by temporary supply of a basic composition to the polish as a function of the measured pH such that the deviation of the measured pH from the target pH during the circulation of the polish between the collecting vessel and the at least one wafer of semiconductor material disposed between the upper and lower polishing platens of the double side polishing machine is at no instant more than ± 0.2 .

Fig. 1